Coatings -- roadmap to readiness

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Why are coatings an issue?



Thermal Noise in IF Mirrors



- Oversimple: kT of energy per mechanical mode, viscous damping
 moves front of mirror w.r.t. center of mass
- For coating dominated noise and structural damping:

aLIGO:
$$\phi_{\text{TiO}_2:\text{Ta}_2\text{O}_5} = 2.3 \times 10^{-4}$$
$$\phi_{\text{SiO}_2} = 4 \times 10^{-5}$$



Basic Coating Concepts

$$\left\langle \Delta x(f,T)^2 \right\rangle \approx \frac{2k_BT}{\pi^2 f} \frac{d}{w^2 Y} \phi(f)$$

- Dielectric mirror
 - alternating high/low index 1/4 wavelength-thick layers
 - large index contrast \Rightarrow fewer required layers: $d \sim 1/(n_H n_L)$
- Key optical properties
 - absorption, scatter ppm's
 - industry standard: ion-beam sputtering
 - R.T. deposition followed by 300 C 500 C annealing
 - scaling to >30 cm nontrivial
 with ~1 nm RMS figure: LMA, Lyon



 $F.O.M.(roughly) \sim \frac{\phi}{n_H - n_L}$

Typical Requirements

	T (K)	λ (μm)	φ /φ _{a-LIGO}	HR abs.	
A+	300	1	1/4	0.5 ppm	
Voyager	123	~2	1/4	2 ppm	
ET-LF	10 – 20?	1.5?	1/3	~1-5 ppm	

- Explorer:
 - A+ or Voyager coating solution can be applied though larger optics and higher power
- No magic bullet solution meets all requirements
 - brief view of physics to motivate approaches
- Present examples of representative approaches

•	Materials	

Materials			
Amorphous	Crystalline		
Oxides	AlGaAs		
Nitrides	AlGaP		
Flourides	AlGaN		
Silicon			
Mix/alloy			
Nano-layers			

Physics			
Amorphous	Crystalline		
Ultrastable/ideal glasses	Dislocations		
Deposition process	Role of contaminants		
Correlation loss-structure	Effect of Stress		
Correlation absorption-structure	Mechanical losses from bonding		
Role of contaminants			

Deposition and related metrology

Deposition technology			
Amorphous	Crystalline		
Uniformity	Uniformity		
Parameter optimisation	Parameter optimisation		
Point defects/scatterer reduction	Point defect reduction		
Post-deposition corrective coatings	Coating transfer		
Elevated temperature deposition	Adhesion		
Post heat treatment (annealing)			
Nano-layered structures			

Metrology				
Thermomechanical	Mechanical loss	TN measurement	Optical Characterisation	
Elastic constants	Clamped systems	AF cantilevers	Complex indices	
Internal stress	Nodal systems	Direct TN mirrors	Thermal coefficients	
Thermal coefficients	Suspended systems			

General Observations About Coating Elastic Loss

Volume rather than interface losses dominate in tantala/silica mirror

D. Crooks, Class. Quantum Grav. 23 (2006) 4953-4965

- current values: Ti:tantala ~5x lossier than silica
- Typical behavior vs temperature and acoustic frequency

(2010)

amorphous materials have loss peak at low temperatures



K.A. Topp, Z. Physik B Condensed Matter 101 235–45 (1996)

Doping and Annealing Alter Dissipation

Loss modified by dopants un-doped tantala ~2kHz 1x10⁻³ 14.5% TiO, doped Ta,O, ~2kHz TiO₂ doping 55% TiO, doped Ta,O, ~2kHz reduces losses in Ta_2O_5 8x10⁻⁴ Mechanical loss increasing Ti 6x10⁻⁴ 4x10⁻⁴ Ti:Ta₂O₅ 2x10⁻⁴ Annealing modifies loss spectra 75 25 50 100 0 Temperature (K) 10 x10⁻⁴ P. Murray et al, U. Glasgow LIGO-G1500874 600°C annealing 9 Coating mechanical loss 400°C temp. 8 300°C 7 Ta_2O_5 annealing modifies behavior 6 can improve loss at some temperatures 5 while worsening it at others 3 annealing temperature limited by crystallization 300 50 100 150 200 250 0 suppressing crystallization important T (K) [I W Martin et al, Class. Quant. Grav. 27 225020, 2010]

Low-frequency losses in amorphous dielectrics

Conventionally associated with low energy excitations (LEEs)
 – conceptualized as two-level systems (TLS)





Oversimple picture: bond flopping

Distribution of TLS in silica due to disordered structure

figures from B.S. Lunin monograph

Theoretical Guidance: Molecular Dynamics

- Molecular dynamics calculations for amorphous materials
 - provide insight into dissipation mechanisms
 - can suggest promising material combinations
- Some observations: simple bond-flopping inadequate picture fails
 - TLS involves dozens of atoms in nm-scale configurations "medium-range" order important



J. Trinastic, R. Hamdan, C. Billman, H. Cheng, Phys. Rev. B93, 014105 (2016)

- Some observations:
 - some theoretical trends tie up with experiment

decrease in loss with titania dopoing in tantala



- Correct trends already suggest potentially interesting materials
 e.g. ZrO₂:Ta₂O₅ (more later)
- Agreement best at cryogenic temperatures larger models being implemented to address 300 K range

Ultrastable Glass: Toy Model



reach more stable glass from vapor than liquid

S. Singh, Nature Mater. 12, 139 (2013)

Ultra-stable Glasses: amorphous silicon (a-Si)

- a-Si experiment: steep improvement for deposition at $T_s \sim 400 \text{ C}$: $\phi \sim 10^{-6}$ (!)
 - much lower loss than deposit at 300 C and anneal at 400 C critical $T_s/T_{glass} \sim 0.75$ vs predicted $T_s \sim 0.8 T_{glass}$
- First example of inorganic ultra-stable glass
 - potential for Voyager mirror coating

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Formation of ultrastable glass favored by:
  Deposition at T_s \sim 0.8 T_{\text{glass}}
  Low deposition rates
  Ion-beam assisted deposition (?)
Applicable to amorphous oxides?
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Amorphous silicon growth simulations



Ultra-stable Oxide Glasses?

18 Metal target - as deposited Ta_2O_5 high T_s deposition Oxide target - as deposited Metal target - annealed 16 Oxide target - annealed lower loss than R.T. dep 14 300 K Loss angle [x 10⁻⁴ rad.] 8 0 0 7 but similar after annealing G Vajente, (2018) Class. Quantum Grav. 35 075001 100 200 400 300 500 600 Deposition temperature [°C] Sputtered Alumina Film Internal Friction vs Temperature Sample135 500C Alumina Sample137 RT Alumina Sample132 300C Alumina um IBS Alumina, 600C anneal BS Silica, 600C anneal AI_2O_3 cryogenic: better than SiO_2 Internal Friction [1/Q] $T_{s} = 300 \text{ C}$ $I_{anneal} = 600 \text{ C}$ preliminary: more characterization necessary 10^{-4} first ultrastable amorphous oxide? $T_{s} = 500 \text{ C}$ M. Abernathy NRL LIGO G1800418 102 10° 10¹

Temperature [K]

- Annealing reduces R.T. loss ~monotonically with T_{anneal}
- Annealing temperature limited by onset of crystallization



- Suppression of crystallization valuable path to low loss
 - chemical frustration

suitable dopants: two cations (Ti:Ta $_2O_5$), three cations ...

geometrical frustration

nanolayers thinner than critical crystal nucleus



- 27%SiO₂:HfO₂
 - HfO₂ crystallizes as deposited
 - SiO₂ suppresses up to 600C anneal $\frac{SO}{2}$ no low-T loss peak (vs SiO₂)
 - no low-T loss peak (vs SiO₂)
 - $-2 \times less loss than SiO_2 at 20 K$
- Revisit for 10 K low-index layer



K. Craig et al, GEO, LIGO-P1800241



I. Martin LIGO-G1801548

Annealing Mixed Oxides: Zr:Ta₂O₅

- Anticipate chemical frustration of crystallization in mixed oxides
- $\sim 15\%$ Zr:Ta₂O₅ shows promising results
 - low rate deposition (S. Reid with ECR)
 - no crystallization up to 750 C (compare ~600 C Ta_2O_5)



- IBS ~48%Zr:Ta₂O₅ up to 800 C (not as good as low-rate 15%Zr:Ta₂O₅)

Structure Determination from X-Ray Scattering



Structural Characterization (Zr:Ta₂O₅)

- Recovered models fit well to data
 - in both short and medium range order
- Clear narrowing of bond-angle distribution with annealing
 - possible connection to high vs low temperature behavior
- Currently computing predicted mechanical loss
 - and responsible motifs



Nanolayers

- Investigate silica with nanolayers of titania
 - NTHU LIGO-G1800300
 - different thicknesses, same ratio
- Cryogenic loss peak suppressed

Low-temperature ϕ suppressed





	threadings (IIII)
SiO ₂	19.3 ± 0.1 (x9)
TiO ₂	8.3 ± 0.2 (x10)
	r = 0.32

	thickness (nm)
SiO ₂	3.6 ± 0.1 (x37)
TiO_2	1.8 ± 0.1 (x38)
	<i>r</i> = 0.33

• Also see crystallization suppression in TiO₂

- Theory ←→ atomic structure ←→ synthesis beginning to interact usefully
 - should speed navigation of experimental parameter space
- Promising results on
 - ideal glass
 - crystallization suppression
- (preliminary) evidence of suitable materials for A+
 not yet fully reproducible
- Non-trivial development time after down-select material
 - depends on how far deposition method is from conventional IBS

- Mechanical properties adequate
 - problems from optical absorption
 - worse at 1 μ m \rightarrow 1.5 μ m \rightarrow 2 μ m
- a-Si
 - Iow-rate ECR deposition
 - 100-fold optical absorption reduction vs conventional IBS
 - add hydrogen annealing?
- a-Si/SiO₂ HR: ~10 ppm abs.
 - apply in MMC

Birney, LIGO-G1801091-v1



Silicon Nitride

- LPCVD deposition of SiN_{0.40}H_{0.79}
 - R.T.: $\phi \sim 1 \ge 10^{-4}$
 - no low temperature loss peak
- 1/4-wave SiN_{0.40}H_{0.79}/SiO₂ bilayers
 - within ~2 of ET-LF and Voyager
 CTN specs
- Optical absorption of SiN/SiO₂ HR: ~50 ppm
 - requires multi-material coating with Ta₂O₅/SiO₂
 - can bring absorption to ~2 ppm
- Annealing behavior studies underway

Pan et al NYHU, P1800164-v3



- Adequate elastic losses available for cryo operation
 - issue in all cases is associated optical absorption
- Multi-material coatings (MMC) a possible solution



J. Steinlechner, et al , *Phys. Rev. D* **91** 042001 (2015) W. Yam et al, *Phys. Rev. D* **91**, 042002 (2015)

10 K Example



Case	bilayers ETM (ITM)	Transmission ETM (ITM) [ppm]	Heat treatment [°C]	CTN ETM (ITM) $[\times 10^{-21} \text{m}/\sqrt{\text{H}}]$	CTN _D [z]	$\alpha_{\rm HR}$ [ppm]
Conventional	$18 (7) \times \mathrm{SiO}_2/\mathrm{Ta}_2\mathrm{O}_5$	4 (8500)	600	3.9(2.3)	6.5	0.6
a-Si	$10 (4) \times \text{SiO}_2: \text{HfO}_2/\text{a-Si}$	2(9000)	400	1.4(0.9)	2.4	11.9
a-Si MMC SiO_2	$\text{Ta}_2\text{O}_5 + 10 (4) \times \text{SiO}_2:\text{HfO}_2/\text{a-Si}$	4.4(6000)	400	1.9 (1.5)	3.4	3.4
ET-LF requirem	ent [12]	5(7000)			≈ 3.4	≤ 5

K. Craig, P1800241-v2

- Absorption and mechanical loss OK for all applications
 - scatter statistics need further characterization
 - uniformity over larger areas



- Scaling to suitable dimensions
 - G. Cole: ~\$40M (GaAs substrate + MBE + bonding tool)
- Note also environmental and thermodynamic tolerances
 - via electro-optic and piezoelectric effects
 - 1 V/cm \rightarrow ~50 nrad Δ reflection phase
 - needs further study

- Timelines to select material system
 - A+LIGO: 2 years
 - cryogenic (Voyager, ET LF): > 5 years
- Research approaches
 - 300 K, 1 μm : amorphous oxides
 - optical ok, elastic needs work
 - cryogenic, 1.5 2 µm, amorphous (crystal?) semiconductors, MMC elastic ok, optical needs work
- Tooling
 - only LMA IBS system currently can meet optical specs compatible with low rates, semiconductor materials?
 - other deposition methods require tool development (\$\$, time)
 ECR sputter: low rate oxide and a-semiconductor
 LPCVD: amorphous semiconductors
 crystal growth + MBE + bonding: AlGaAs crystal mirrors
 - how/when to begin to develop alternative tools?

Path(s) Forward for Cryogenic 3G Coatings

As simple as it can be, but no simpler

- Amorphous semiconductors
 - continue to explore parameter space to reduce absorption rate, temperature, annealing temperature and atmosphere
- Multi-material mirrors
 - test optical properties and thermal noise on complete HRs
 - explore alternative low-index oxide layers nanolayers to suppress crystallization/loss?
- Alternative deposition methods to IBS
 - low-rate ECR, LPCVD
 - better material properties obtained than IBS
 - realistic for scaled-up mirrors?

fab small HRs, evaluate scatter etc

evaluate tooling cost (and time) to adapt to 3G-scale mirrors

- Crystalline mirrors
 - best absorption and thermal noise combination
 - more complete scatter statistics useful
 - electro-optic and piezoelectric properties

evaluate thermodynamic and environmental implications

- scaling expensive